

1N5400 - 1N5408 AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50-1000V CURRENT: 3.0 A

Features

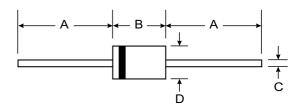
- High Current Capability and Low Forward Voltage Drop
- Low Reverse Leakage Current
- Plastic Material: UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: DO-201AD
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Mounting Position: Any
- Marking: Type Number
- Weight: 1.1 grams (approx.)







DO-201AD							
Dim	Min	Мах					
Α	25.40	_					
В	7.20	9.50					
С	1.20	1.30					
D	4.80	5.30					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

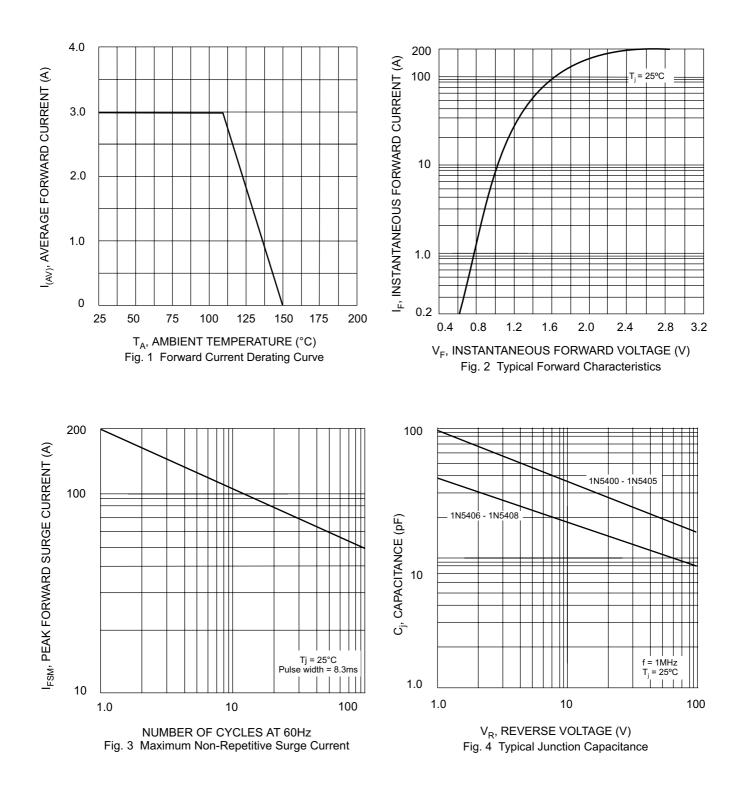
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	1N 5400	1N 5401	1N 5402	1N 5404	1N 5406	1N 5407	1N 5408	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current @ T _A = 105°C (Note 1		3.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		200						A	
Forward Voltage $@ I_F = 3.04$	A V _{FM}	1.0						V	
Peak Reverse Current $@ T_A = 25^{\circ}C$ at Rated DC Blocking Voltage $@ T_A = 150^{\circ}C$		RM 10 100			μA				
Typical Junction Capacitance (Note 2) C _j	50 25						pF	
Typical Thermal Resistance Junction to Ambient		15						K/W	
Operating and Storage Temperature Range		-65 to +150							°C

Notes: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.





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单击下面可查看定价,库存,交付和生命周期等信息

>>SUNMATE(森美特)